

Reliability Of High Mobility SiGe Channel MOSFETs For Future CMOS Applications (Springer Series In Advanced Microelectronics) By Jacopo Franco;Ben Kaczer;Guido Groeseneken

By Jacopo Franco;Ben Kaczer;Guido Groeseneken

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SiGe channel MOSFETs for future CMOS applications. [Jacopo Springer series in advanced microelectronics, Jacopo Franco, Ben Kaczer, Guido Groeseneken. <http://www.worldcat.org/title/reliability-of-high-mobility-sige-channel-mosfets-for-future-cmos-applications/oclc/863151654>

Reliability of SiGe channel MOS enhanced mobility and pMOS threshold voltage tuning [7]. including a high Ge fraction (55%) in the <http://ma.ecsdl.org/content/MA2012-02/43/3119.full.pdf>

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SiGe Channel Technology: Superior Reliability improved NBTI reliability for this family of high-mobility (Si and SiGe) high-kmetal gate CMOS technology with

http://www.iue.tuwien.ac.at/pdf/ib_2012/JB2012_Grasser_5.pdf

ESD characterization of high mobility SiGe Quantum Well and Ge is the use of High Mobility the ESD reliability of such a technology option is

<http://ieeexplore.ieee.org/iel5/6327836/6333279/06333355.pdf?arnumber=6333355>

Ben Kaczer is the author of Reliability of High Mobility Sige Channel Mosfets for Future CMOS Applications (0.0 avg rating, 0 ratings, 0 reviews, publish

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which is based on silicon germanium [20] AlGaAs/InGaAs pseudomorphic high electron mobility High-reliability GaAs-AlGaAs HBTs by MBE

<http://www.nepp.nasa.gov/DocUploads/FA968B63-F711-46F4-95CE441207843BC1/NEPP-TRO-GaAs%20RF.doc>

(INVITED) High Reliability/Supply Chain Risks Daniel Marrujo, DMEA BTI Reliability of High Mobility Channel Devices: SiGe, Ge, and InGaAs Jacopo Franco, IMEC

http://www.iirw.org/fileadmin/user_upload/2014progScheduleV333-1014.pdf

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<http://www.springer.com/?SGWID=4-102-66-653429-0&sba=INCLUDE&originalID=531224&resultStart=711>

The potential applications of strained SiGe alloys to high to their high carrier mobility, reliability also suggests that the high

<http://iopscience.iop.org/0268-1242/18/1/305/fulltext/>

Enrico Zanoni(5) Guido Groeseneken(5) Impact of Off State Stress on advanced high-K metal gate NMOSFETs. (sSOI substrate, SiGe channel) planar FDSOI MOSFETs.

http://dblp.l3s.de/?q=ESSDERC&search_opt=venuesOnlyExact&newQuery=yes&resTableName=query_result3j2G5b&resultsPerPage=100

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<http://www.ellibs.com/book/9789400776630/reliability-of-high-mobility-sige-channel-mosfets-for-future-cmos-applications>

NBTI Reliability of SiGe and Ge Channel pMOSFETs With SiO₂ reliability of SiGe channel pMOSFETs: interests focus on the reliability of high-mobility
http://www.iue.tuwien.ac.at/pdf/ib_2013/JB2014_Grasser_2.pdf

of High Mobility SiGe Channel MOSFETs for Future CMOS Applications
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<http://www.amazon.co.jp/Reliability-Mobility-Applications-Springer-Microelectronics/dp/9400776624>

Future Students; Graduate Admissions CMOS Circuits for Piezoelectric Energy Harvesters : Efficient Power Extraction, Dordrecht : Springer, 2014 Online Access:

<http://catalog.uttyler.edu/cgi-bin/koha/opac-search.pl?q=se:Springer%20series%20in%20advanced%20microelectronics>,

the Impacts of Hydro Projects on People and the Environment in China Pu Wang, Shikui Dong, James Lassoie (auth.) 2014 Springer Netherlands

<http://wp.lumbungbuku.com/2014/12/1994-referensi-textbook-journal-theses-dissertation/>

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http://wdn2.ipublishcentral.com/springer_verlag_gmbh/viewinside/500168843568711

12-6-2010 Intrinsic Reliability Improvement in Biaxially Strained SiGe p-MOSFETs due to its high hole mobility and at SiGe/high-k as

http://www.academia.edu/2835462/Intrinsic_reliability_improvement_in_biaxially_strained_SiGe_p-MOSFETs

the introduction of high mobility silicon germanium SiGe pFETs appear to be able to reach the current ITRS reliability targets. Band structure of SiGe

<http://semiengineering.com/reliability-after-planar-silicon/>

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Abstract. With a significantly reduced Negative Bias Temperature Instability (NBTI), SiGe channel pMOSFETs promise to virtually eliminate this reliability issue for

<http://www.sciencedirect.com/science/article/pii/S0167931713002074>

and silicon germanium have received significant the buried Si_{0.4}Ge_{0.6} serves as a high mobility p- reliability concern in some of these devices is the shift of

http://www-mtl.mit.edu/research/annual_reports/2003/elec_devices.pdf

and U. K. Mishra, Proton irradiation effects on GaN-based high electron mobility the reliability of high-K Available High-Speed SiGe

<http://www.isde.vanderbilt.edu/rer/publications/2004-journal-articles/>

Sep 29, 2008 SEMATECH Research on Reliability of Workfunction Controlled High-k Metal Gates Recognized by * High Mobility SiGe Channel pMOSFETs

<http://www.thefreelibrary.com/SEMATECH+Research+on+Reliability+of+Workfunction+Controlled+High-k...-a0186012734>

we have fabricated high mobility SiGe channel pMOSFETs after optimizing epitaxial Reliability of Strained SiGe Channel p-Channel Metal?Oxide

<http://iopscience.iop.org/1347-4065/48/4S/04C055>

We evaluated the thermal reliability of thin SiGe epilayers High Ge-content strained SiGe-on-Si is a useful channel material in high-mobility SiGe

<http://www.sciencedirect.com/science/article/pii/S0169433211020174>

and diborane sources for the preparation of the B-doped Si This high mobility of the CVD SiGe lm by CVD and annealed at high temperature, the reliability of

<http://www.jim.or.jp/journal/e/pdf3/50/07/1596.pdf>

During the last decade many new concepts have been proposed for improving the performance of power MOSFETs. The results of this research are dispersed in the

http://www.ciao.de/sr/q-mosfet_tc-750808